





40V 1A GATE DRIVER IN SOT26

Description

ZXGD3009E6 is a high-speed non-inverting single gate driver for switching MOSFETs. It can transfer up to 1A peak source/sink current into the gate for effective charging and discharging the capacitive gate load.

This gate driver ensures rapid switching of the MOSFET to minimize power losses and distortion in high current switching applications. It can typically drive 500mA into the low gate impedance with just 10mA input from a controller. The turn-on and turn-off switching behavior of the MOSFET can be individually tailored to suit an application. By defining the switching characteristics appropriately, EMI and cross conduction can be reduced.

Features

- High-Gain Buffer With Typically 500mA Output from 10mA Input
- Rugged Emitter-Follower to Latch-up/Shoot-Through Issues
- Wide Supply Voltage to Minimize On-Losses
- Optimized Pin-Out to Simplify PCB Layout and Reduce Parasitic Trace Inductances
- Near-Zero Quiescent Supply Current
- Qualified to AEC-Q101 Standards for High Reliability
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

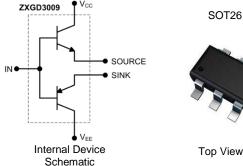
Applications

Power MOSFET Gate Driving in:

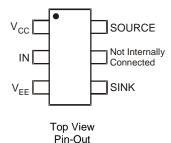
- AC-DC Power Supplies (SMPS)
- **DC-DC Converters**
- DC-AC Inverters (i.e. Solar)
- 1-, 2-, and 3-Phase Motor Control Circuits
- **Amplifier Output Stages**

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.018 grams (Approximate)







Pin Name	Pin Function
V _{CC}	Supply Voltage High
IN	Driver Input
VEE	Supply Voltage Low
SOURCE	Source Current Output *
SINK	Sink Current Output *

^{*} Typically connect SOURCE & SINK together

Ordering Information (Note 4)

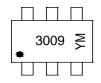
Ī	Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
	ZXGD3009E6TA	AEC-Q101	3009	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain < 900ppm bromine, < 900ppm chlorine (< 1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

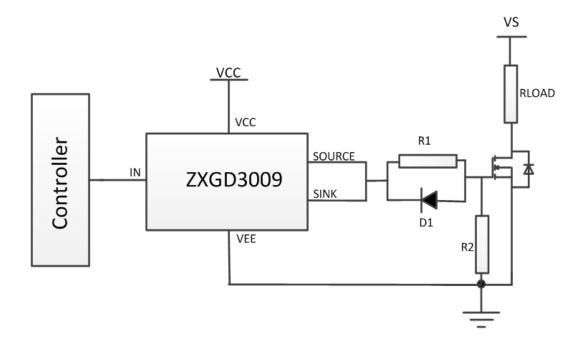


3009 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2018	3	2019	2020	2021	2022	2023	2024	4 20	25	2026	2027	2028
Code	F		G	Н	ı	J	K	L	N	Л	N	Р	Q
Mont	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	,	1	2	3	4	5	6	7	8	9	0	N	D

Typical Application Circuit



R1, D1 combination can be used for variable turn on and turn off times.



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage, with Respect to V _{EE}	V _{CC}	40	V
Input Voltage, with Respect to V _{EE}	V _{IN}	40	V
Output Difference Voltage (Source – Sink)	$\Delta V_{(source-sink)}$	±7	V
Peak Pulsed Output Current (Source and Sink)	I _{OM}	±2	Α
Peak Pulsed Input Current	I _{IM}	±1	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Notes 5 & 6)	D	1.1	W
Linear Derating Factor	P _D	8.8	mW/°C
Thermal Resistance, Junction to Ambient (Notes 5 & 6)	R _Ð JA	113	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{ÐJL}	105	- C/VV
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristics	Symbols	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with pin 1 (V_{CC}) and pin 3 (V_{EE}) on 25mm × 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in steady-state. The heatsink is split in half with pin 1 (V_{CC}) and pin 3 (V_{EE}) connected separately to each half.
- 6. For device with two active die running at equal power.
- 7. Thermal resistance from junction to solder-point at the end of each lead on pin 1 (V_{CC}) and pin 3 (V_{EE}).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

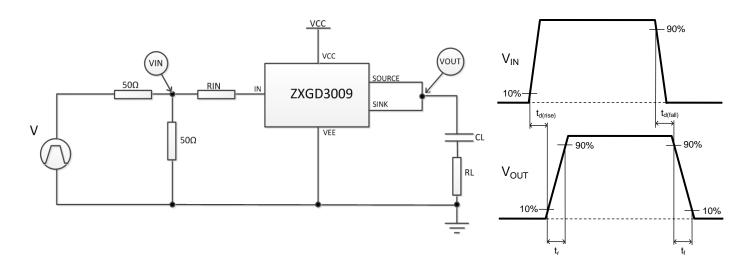


Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

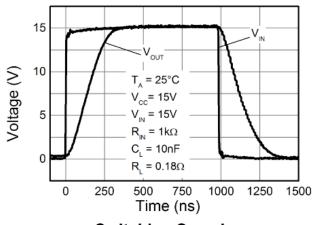
Characteristic	Symbol	Min	Тур	Max	Unit		Test Condition	
Output Voltage, High	V _{OH}	V _{CC} - 0.8	V _{CC} - 0.4	_	V	$I_{(source)} = 1\mu A, V_{IN} = V_{CC}$		
Output Voltage, Low	V _{OL}	_	V _{EE} + 0.2	V _{EE} + 0.5	V	$I_{(sink)} = 1\mu A, V_{IN} = V_{EE}$		
Supply Breakdown Voltage	BVcc	40	_	_	V	$I_Q = 100 \mu A, V$	$IN = V_{CC}$	
Supply Breakdown Voltage	PACC	40	_	_	v	$I_Q = 100 \mu A, V$	$IN = V_{EE} = 0V$	
Quiescent Supply Current	ΙQ		_	20	nA	$V_{CC} = 32V, V_{II}$	$V = V_{CC}$	
Quiescent Supply Surrent	'Q	_	_	20	11/4	V _{CC} = 32V, V _{IN}	= V _{EE} = 0V	
Peak Pulsed Source Current	I _{(source)M}	_	0.98	_	Α	I _{IN} = 10mA, V _C	C = 5V, VOUT= 0V	
Peak Pulsed Sink Current	I _{(sink)M}	_	0.78	_		I _{IN} = -10mA, V _E	EE = 0V, VOUT= 5V	
Peak Pulsed Source Current	I _{(source)M}	_	1.58	_	Α	I _{IN} = 50mA, V _C	C = 5V, VOUT= 0V	
Peak Pulsed Sink Current	I _{(sink)M}	_	1.38	_	,,	I _{IN} = -50mA, V _E	EE = 0V, VOUT= 5V	
Peak Pulsed Source Current with Varying Input Resistances	I _{(source)M}	_	0.74 0.175 0.019	_	А	$R_{IN} = 100\Omega$ $R_{IN} = 1k\Omega$ $R_{IN} = 10k\Omega$	$\begin{split} &V_{CC}=15V,V_{EE}=0V\\ &V_{IN}=15V\\ &C_L=1nF,R_L=0.18\Omega\\ &R_{SOURCE}=0\Omega,R_{SINK}=0\Omega \end{split}$	
Peak Pulsed Sink Current with Varying Input Resistances	I(sink)M	_	1.05 0.22 0.025	_	Α	$R_{IN} = 100\Omega$ $R_{IN} = 1k\Omega$ $R_{IN} = 10k\Omega$	$\begin{split} &V_{CC}=15V,V_{EE}=0V\\ &V_{IN}=15V\\ &C_L=1nF,R_L=0.18\Omega\\ &R_{SOURCE}=0\Omega,R_{SINK}=0\Omega \end{split}$	
Switching Times with Low Input Resistance	t _{d(rise)} t _r t _{d(fall)}	_	3.8 15 4 15	-	ns	$\begin{aligned} &V_{CC} = 12 \text{V}, V_{E} \\ &V_{IN} = 0 \text{ to } 10 \text{V} \\ &R_{IN} = 25 \Omega \\ &C_{L} = 1 \text{nF}, R_{L} = \\ &R_{SOURCE} = 0 \Omega \end{aligned}$	· 0.18Ω	
Switching Times with Low Load Capacitance $C_L = 1nF$	t _{d(rise)} t _r t _{d(fall)}	_	18 36 16 40	_	ns	$V_{CC} = 15V, V_{E}$ $V_{IN} = 0 \text{ to } 15V$ $R_{IN} = 1k\Omega$ $C_{L} = 1nF, R_{L} = R_{SOURCE} = 0\Omega$	- 0.18Ω	
Switching Times with High Load Capacitance $C_L = 10nF$	$\begin{array}{c} t_{d(rise)} \\ t_{r} \\ t_{d(fall)} \\ t_{f} \end{array}$	_	47 210 39 240	_	ns	$\begin{aligned} &V_{CC} = 15 \text{V}, \ V_{E} \\ &V_{IN} = 0 \text{ to } 15 \text{V} \\ &R_{IN} = 1 \text{k} \Omega \\ &C_{L} = 10 \text{nF}, \ R_{L} \\ &R_{SOURCE} = 0 \Omega \end{aligned}$	= 0.18Ω	

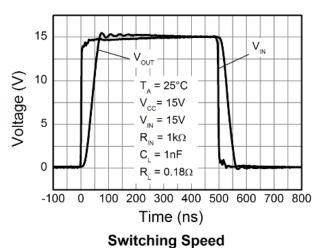


Switching Test Circuit and Timing Diagram



Typical Switching Characteristics (@ T_A = +25°C, unless otherwise specified.)





Switching Speed

T_A = 25°C

V_{cc} = 15V
V_N = 15V
Square Wave

C_L=10nF

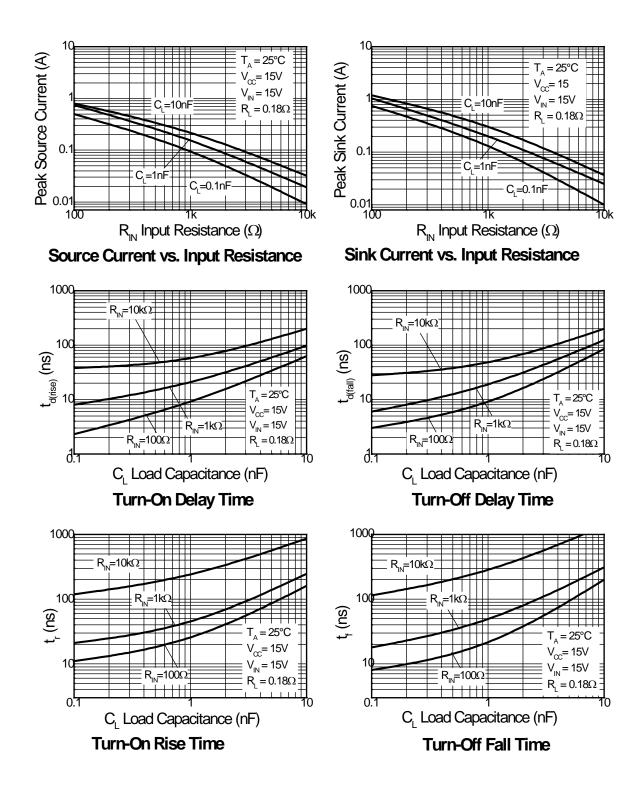
1E-4
10
100
1k
10k
100k
1M
(Frequency (Hz))

Supply Current

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Datasheet Number: DS36885 Rev. 3 - 2 www.diodes.com



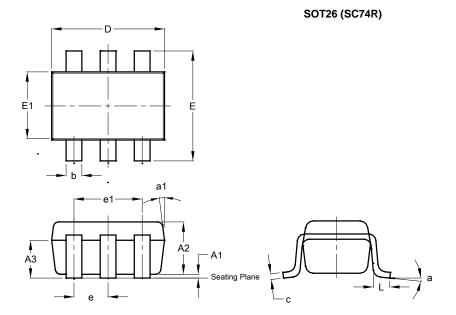
Typical Switching Characteristics (@ T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

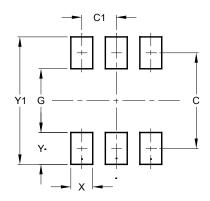


;	SOT26 (SC74R)							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	_	_	0.95					
e1	_	_	1.90					
E	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	_		8°					
a1	_		7°					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26 (SC74R)



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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